

FDMS2572

N-Channel UltraFET Trench® MOSFET

150V, 27A, 47mΩ

Features

- Max $r_{DS(on)}$ = 47mΩ at V_{GS} = 10V, I_D = 4.5A
- Max $r_{DS(on)}$ = 53mΩ at V_{GS} = 6V, I_D = 4.5A
- Low Miller Charge
- Optimized efficiency at high frequencies
- UIS Capability (Single pulse and Repetitive pulse)
- RoHS Compliant

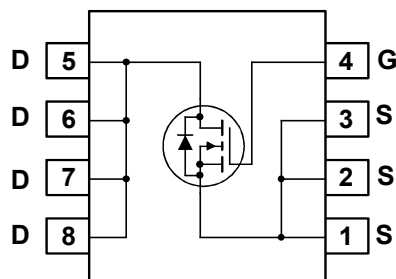
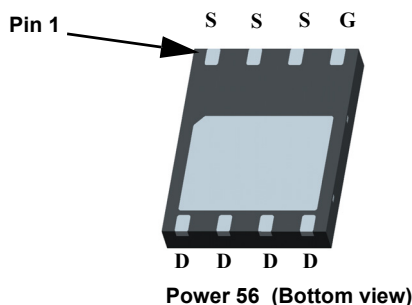


General Description

UltraFET devices combine characteristics that enable benchmark efficiency in power conversion applications. Optimized for $r_{DS(on)}$, low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

Application

- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	150	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	27	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	27	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	4.5	
	-Pulsed	30	
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	78	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.6	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS2572	FDMS2572	Power 56	13"	12mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		180		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120\text{V}$, $V_{GS} = 0\text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$			± 100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2	3	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-9.8		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 4.5\text{A}$		36	47	m Ω
		$V_{GS} = 6\text{V}$, $I_D = 4.5\text{A}$		39	53	
		$V_{GS} = 10\text{V}$, $I_D = 4.5\text{A}$, $T_J = 125^\circ\text{C}$		69	103	
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{V}$, $I_D = 4.5\text{A}$		14		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 75\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		1960	2610	pF
C_{oss}	Output Capacitance			130	175	pF
C_{rss}	Reverse Transfer Capacitance			30	45	pF
R_g	Gate Resistance	$f = 1\text{MHz}$		1.3		Ω

Switching Characteristics

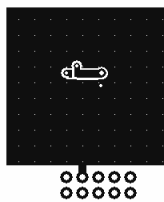
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{V}$, $I_D = 1.0\text{A}$ $V_{GS} = 10\text{V}$, $R_{GEN} = 6\Omega$		11	20	ns
t_r	Rise Time			8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			38	61	ns
t_f	Fall Time			31	50	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V}$ to 10V	$V_{DD} = 75\text{V}$ $I_D = 4.5\text{A}$	31	43	nC
Q_{gs}	Gate to Source Gate Charge			9		nC
Q_{gd}	Gate to Drain "Miller" Charge			7		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 2.2\text{A}$ (Note 2)		0.7	1.0	V
t_{rr}	Reverse Recovery Time	$I_F = 4.5\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		67	101	ns
Q_{rr}	Reverse Recovery Charge			130	195	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $50^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b. $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

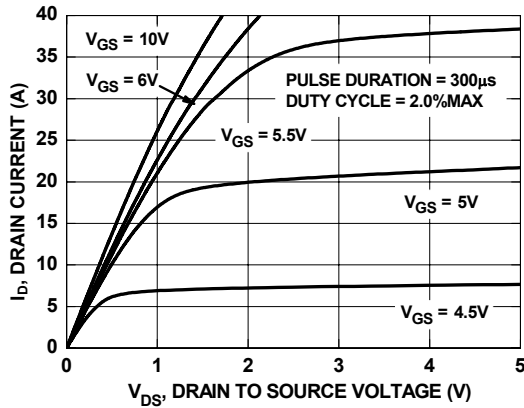


Figure 1. On-Region Characteristics

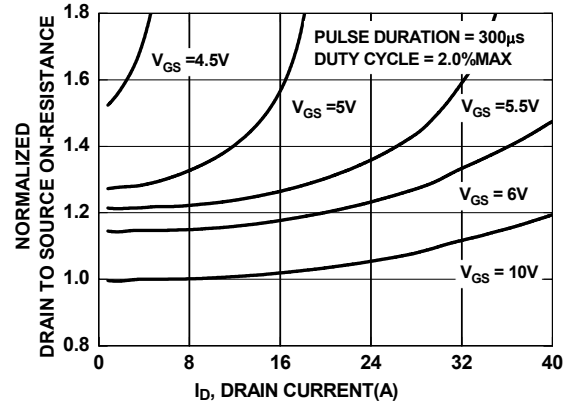


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

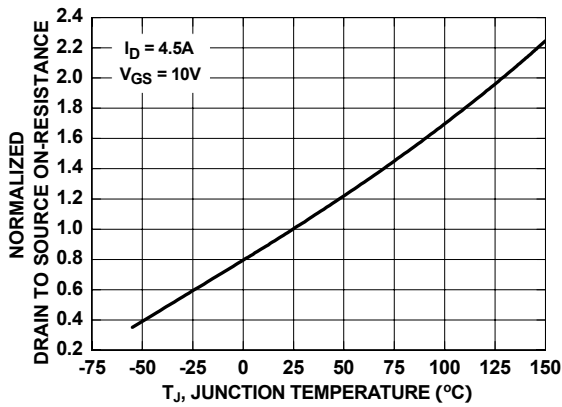


Figure 3. Normalized On-Resistance vs Junction Temperature

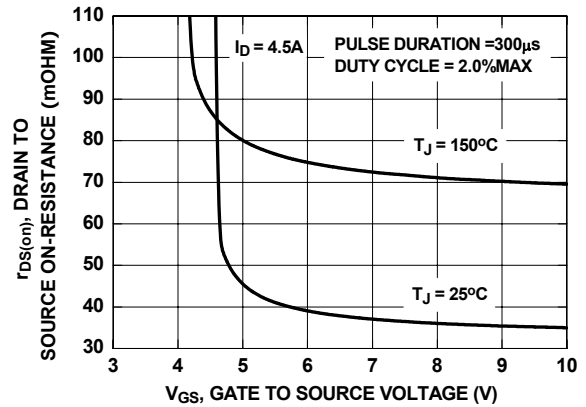


Figure 4. On-Resistance vs Gate to Source Voltage

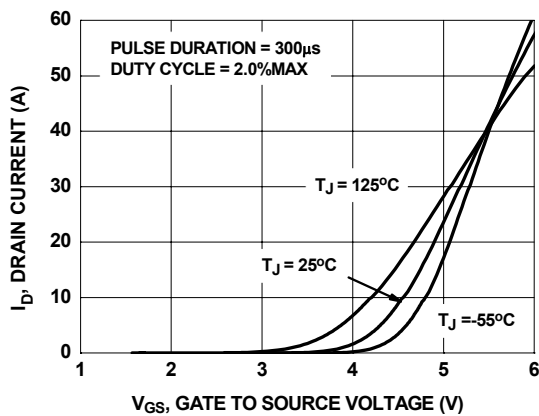


Figure 5. Transfer Characteristics

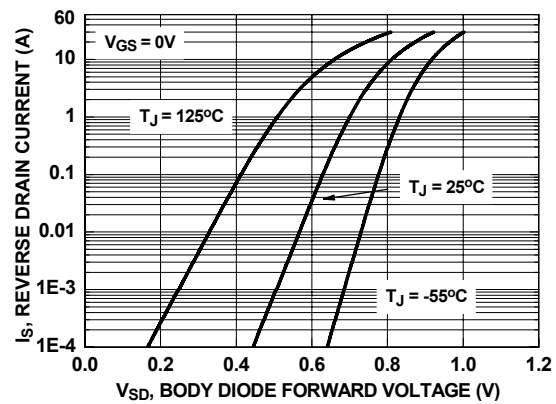


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

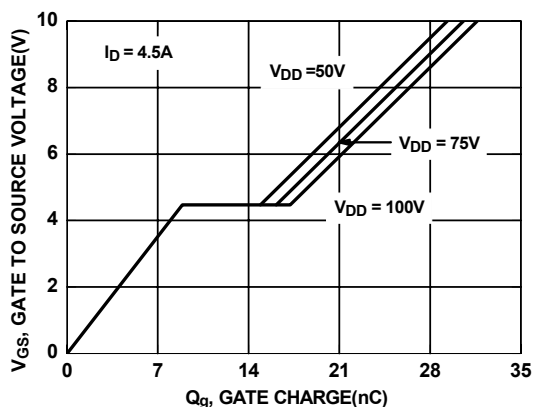


Figure 7. Gate Charge Characteristics

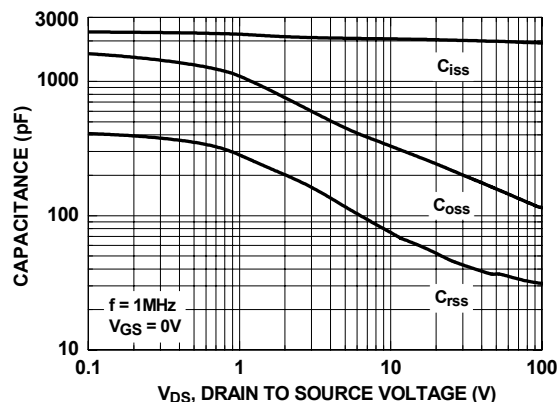


Figure 8. Capacitance vs Drain to Source Voltage

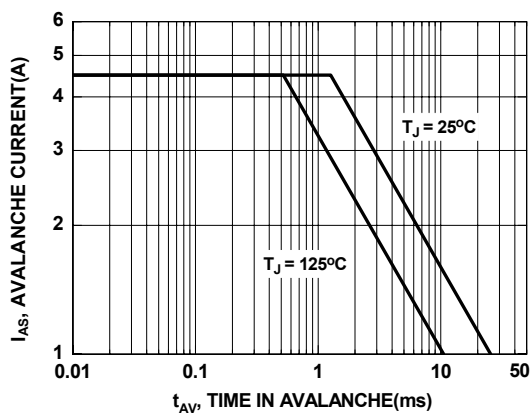


Figure 9. Unclamped Inductive Switching Capability

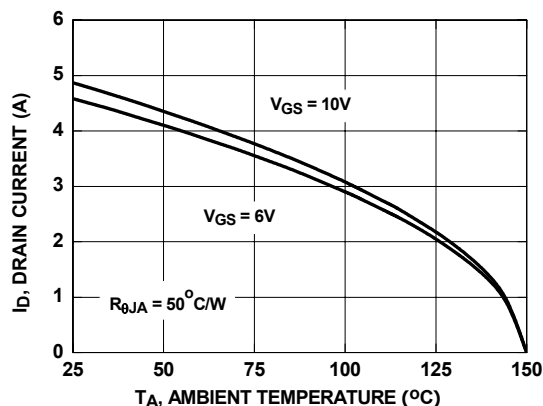


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

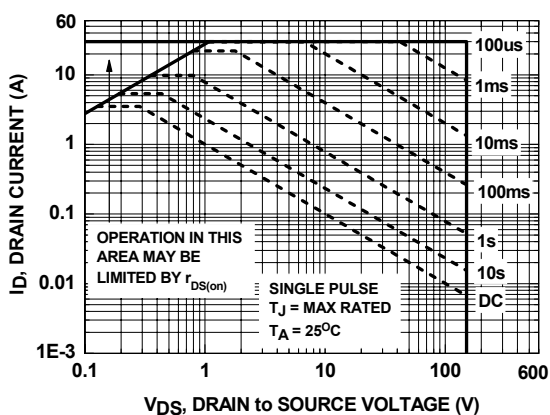


Figure 11. Forward Bias Safe Operating Area

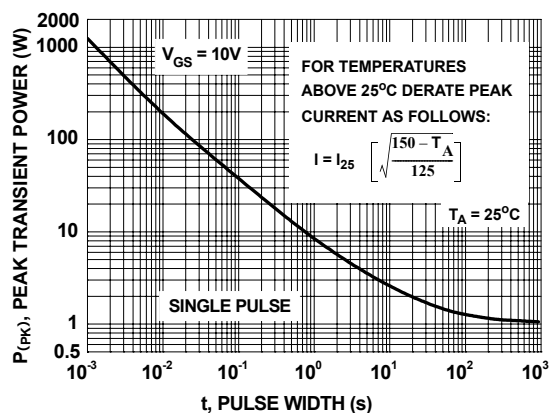
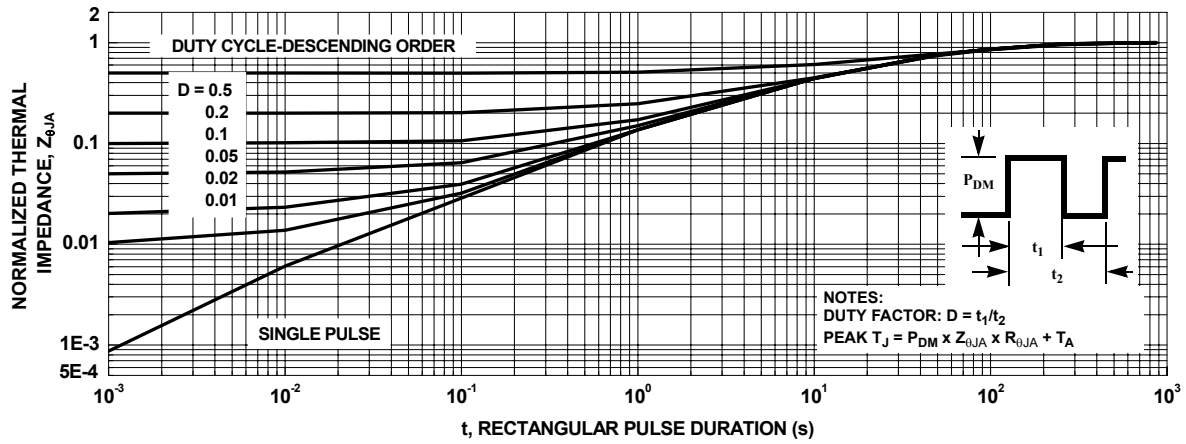
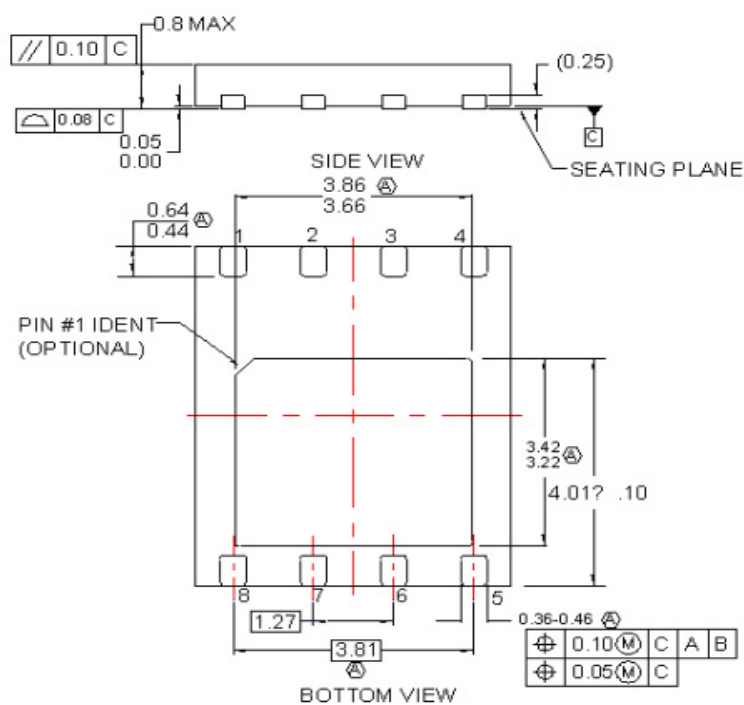
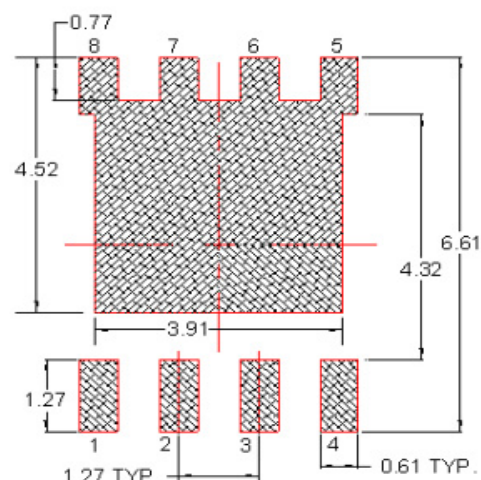
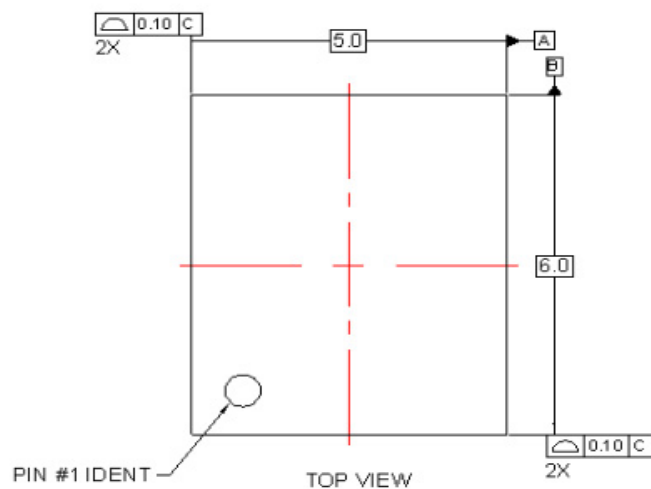


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted





NOTES:

- ☒ A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229. DATED 11/2001.
- ☐ B. DIMENSIONS ARE IN MILLIMETERS.
- ☐ C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
- ☐ D. TERMINALS 5,6,7 AND 8 ARE TIED TO THE EXPOSED PADDLE

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